# RT1P441X SERIES

〈Transistor〉 Transistor With Resistor For Switching Application Silicon PNP Epitaxial Type

UNIT:mm

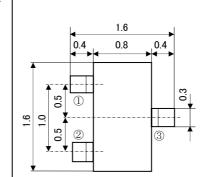
OUTLINE DRAWING

#### DESCRIPTION

RT1P441X is a one chip transistor with built-in bias resistor,NPN type is RT1N441X.

#### FEATURE

•Built-in bias resistor (R1=47k $\Omega$ ,R2=47k $\Omega$ ).



0.1

JEITA : -

JEDEC : -

**Terminal Connector** 

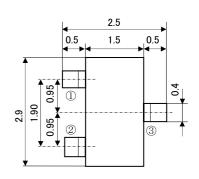
1):Base

2: Emitter

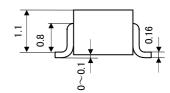
3: Collector

2

RT1P441U



RT1P441C



JEITA:SC-59 JEDEC:Similar to TO-236

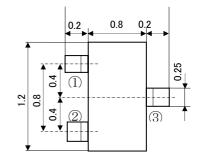
**Terminal Connector** 

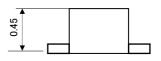
①:Base

2:Emitter

③:Collector

RT1P441T

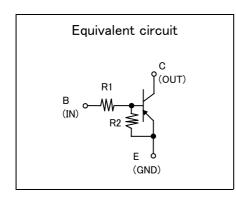




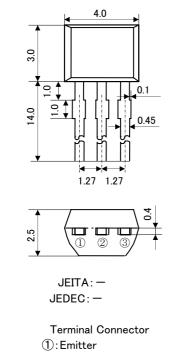
JEITA: —
JEDEC :
Terminal Connector
①:Base
2:Emitter
③:Collector

#### **APPLICATION**

Inverted circuit, switching circuit, interface circuit, driver circuit.





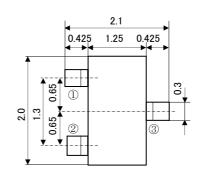


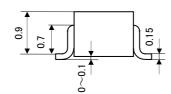
2: Collector

③:Base

RT1P441M

0.7





JEITA: SC-70 JEDEC: — Terminal Connector ①:Base ②:Emitter ③:Collector

ISAHAYA ELECTRONICS CORPORATION

# **RT1P441X SERIES**

(Transistor)

Transistor With Resistor

For Switching Application

Silicon PNP Epitaxial Type

## MAXIMUM RATING (Ta=25°C)

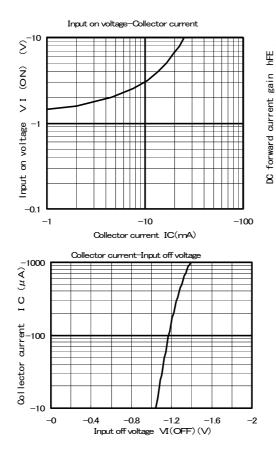
SYMBOL	PARAMETER	RATING						
STWIDUL	PARAMETER	RT1P441T	RT1P441U	RT1P441M	RT1P441C	RT1P441S	UNIT	
V <sub>CBO</sub>	Collector to Base voltage	-50					V	
V <sub>EBO</sub>	Emitter to Base voltage	-10					V	
V <sub>CEO</sub>	Collector to Emitter voltage	-50					V	
Ι <sub>c</sub>	Collector current	-100					mA	
I <sub>CM</sub>	Peak Collector current	-200					mA	
Pc	Collector dissipation(Ta=25°C)	125(※)	125	1	50	450	mW	
Tj	Junction temperature	+125		+150			°C	
Tstg	Storage temperature	-55~+125		-55~+150			°C	

(%) package mounted on 9mm × 19mm × 1mm glass-epoxy substrate.

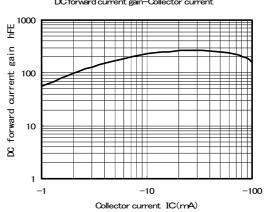
### ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
		TEST CONDITION	MIN	TYP	MAX	UNIT
V <sub>(BR)CEO</sub>	C to E break down voltage	$I_{c} = -100 \mu A, R_{BE} = \infty$	-50			V
I <sub>CBO</sub>	Collector cut off current	V <sub>CB</sub> =-50V, I <sub>E</sub> =0			-0.1	μA
h <sub>FE</sub>	DC forward current gain	V <sub>CE</sub> =-5V, I <sub>C</sub> =-5mA	50			
$V_{CE(sat)}$	C to E saturation voltage	I <sub>c</sub> =–10mA, I <sub>B</sub> =–0.5mA		-0.1	-0.3	V
V <sub>I(ON)</sub>	Input on voltage	$V_{ce}$ =-0.2V, I <sub>c</sub> =-5mA		-2.3	-5.0	V
V <sub>I(OFF)</sub>	Input off voltage	$V_{ce}$ =-5V, I <sub>c</sub> =-100 $\mu$ A	-0.8	-1.1		V
R <sub>1</sub>	Input resistance		33	47	61	kΩ
$R_2 / R_1$	Resistance ratio		0.9	1.0	1.1	
f⊤	Gain band width product	V <sub>CE</sub> =-6V, I <sub>E</sub> =10mA		150		MHz

### **TYPICAL CHARACTERISTICS**



DC forward current gain-Collector current



## ISAHAYA ELECTRONICS CORPORATION



Marketing division, Marketing planning department

6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

#### Keep safety first in your circuit designs!

ISAHAYA Electronics Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (1) placement of substitutive, auxiliary, (2) use of non-farmable material or (3) prevention against any malfunction or mishap.

#### Notes regarding these materials

These materials are intended as a reference to our customers in the selection of the ISAHAYA products best suited to the customer's application; they don't convey any license under any intellectual property rights, or any other rights, belonging

Customer's application; they don't convey any license under any intellectual property rights, or any other rights, belonging ISAHAYA or third party. ISAHAYA Flectronics Corporation assumes no responsibility for any damage, or infringement of any third party's rights, originating in the use of any product data, diagrams, charts or circuit application examples contained in these materials. •All information contained in these materials, including product data, diagrams and charts, represent information on products at the time of publication of these materials, and are subject to change by ISAHAYA Electronics Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact ISAHAYA Electronics Corporation or an authorized ISAHAYA products distributor for the latest product information before purchasing product listed backing. hereir

ISAHAYA Electronics Corporation products are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact ISAHAYA electronics corporation or an authorized ISAHAYA products distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
The prior written approval of ISAHAYA Electronics Corporation is necessary to reprint or reproduce in whole or in part these

materials.

If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination. Any diversion or re-export contrary to be export control laws and regulations of Japan and/or the country of destination is prohibited. •Please contact ISAHAYA Electronics Corporation or authorized ISAHAYA products distributor for further details on these

materials or the products contained therein.